

DYNAMIC CHARACTERISTICS

APT30DQ120BCT(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25^\circ C$	-	26		ns
t_{rr}	Reverse Recovery Time	$I_F = 30A$, $di_F/dt = -200A/\mu s$ $V_R = 800V$, $T_C = 25^\circ C$	-	320		
Q_{rr}	Reverse Recovery Charge		-	545		nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30A$, $di_F/dt = -200A/\mu s$ $V_R = 800V$, $T_C = 125^\circ C$	-	435		ns
Q_{rr}	Reverse Recovery Charge		-	2100		nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30A$, $di_F/dt = -1000A/\mu s$ $V_R = 800V$, $T_C = 125^\circ C$	-	180		ns
Q_{rr}	Reverse Recovery Charge		-	2975		nC
I_{RRM}	Maximum Reverse Recovery Current		-	28		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.80	$^\circ C/W$
W_T	Package Weight		0.22		oz
			5.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

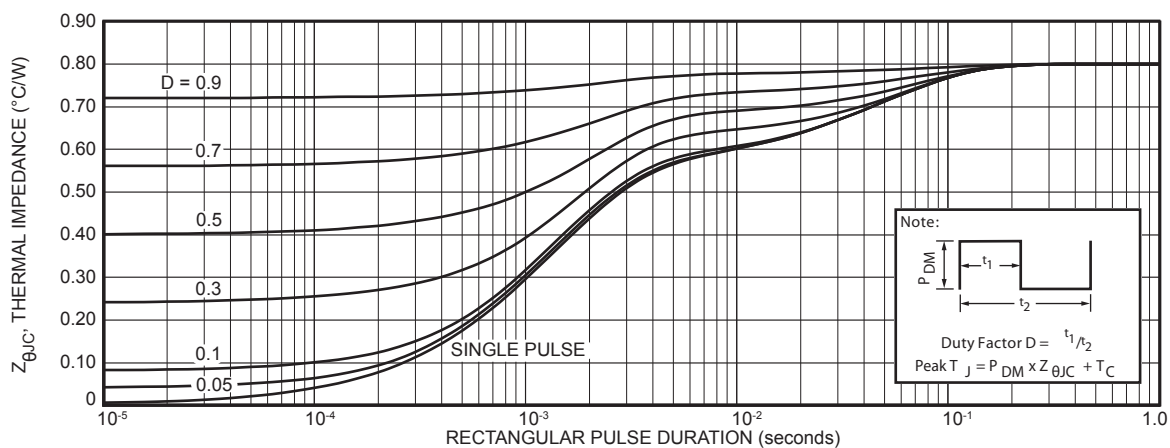


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT30DQ120B_S(G)

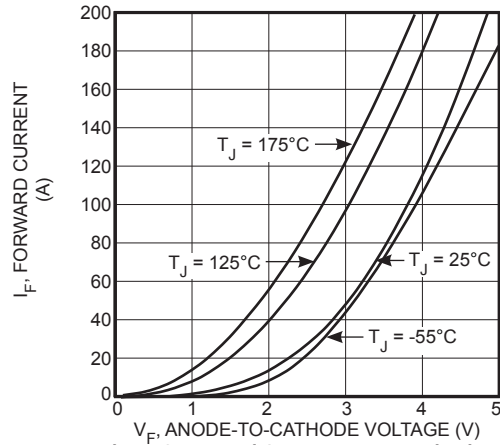


Figure 2. Forward Current vs. Forward Voltage

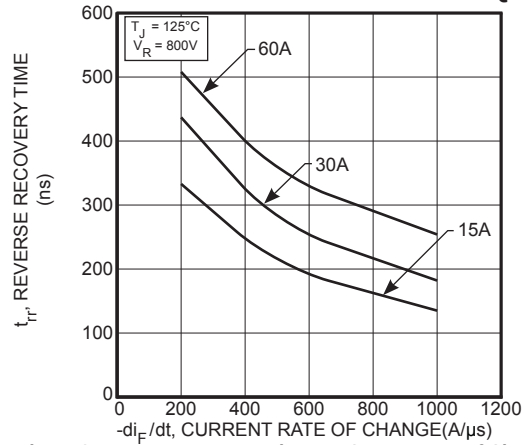


Figure 3. Reverse Recovery Time vs. Current Rate of Change

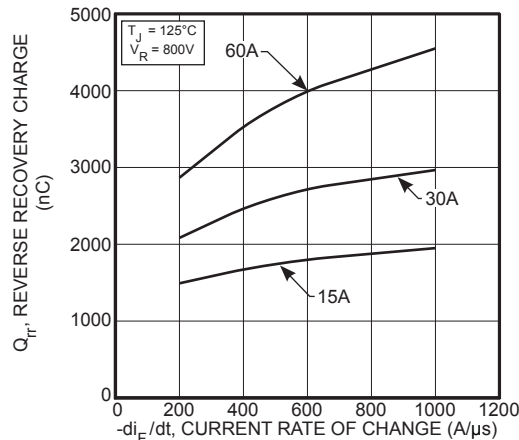


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

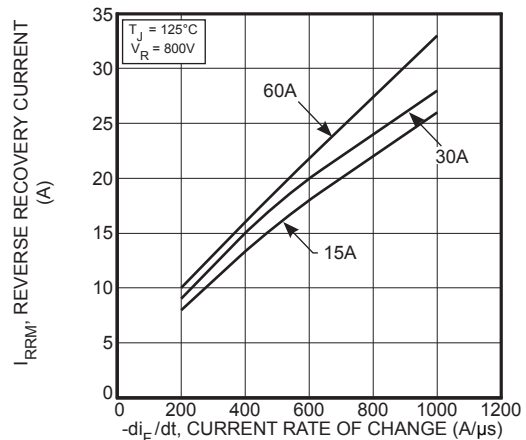


Figure 5. Reverse Recovery Current vs. Current Rate of Change

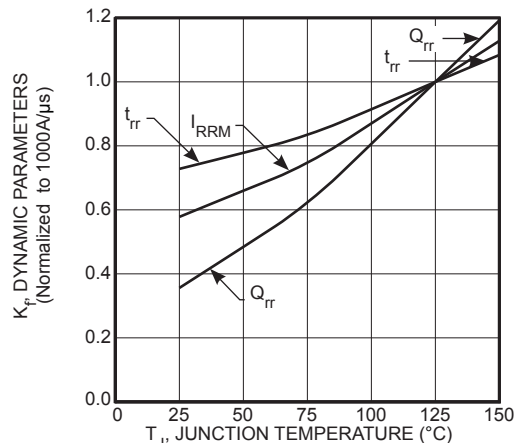


Figure 6. Dynamic Parameters vs. Junction Temperature

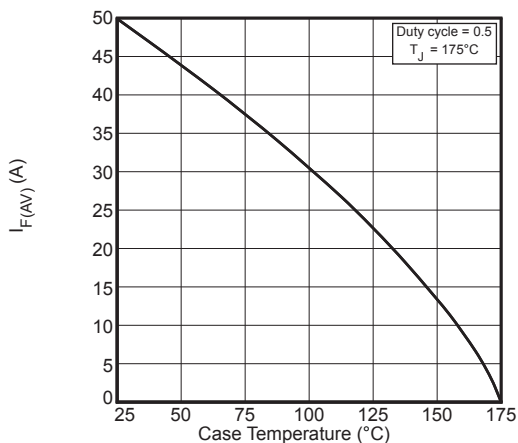


Figure 7. Maximum Average Forward Current vs. Case Temperature

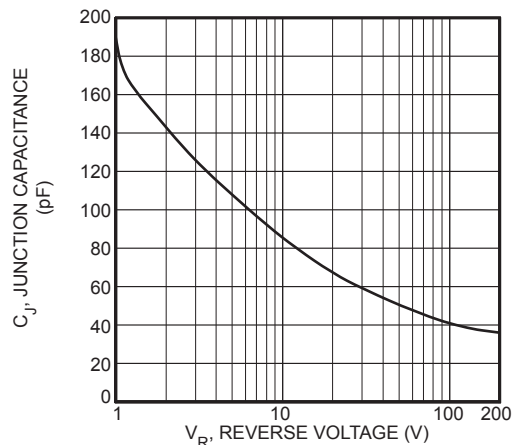


Figure 8. Junction Capacitance vs. Reverse Voltage

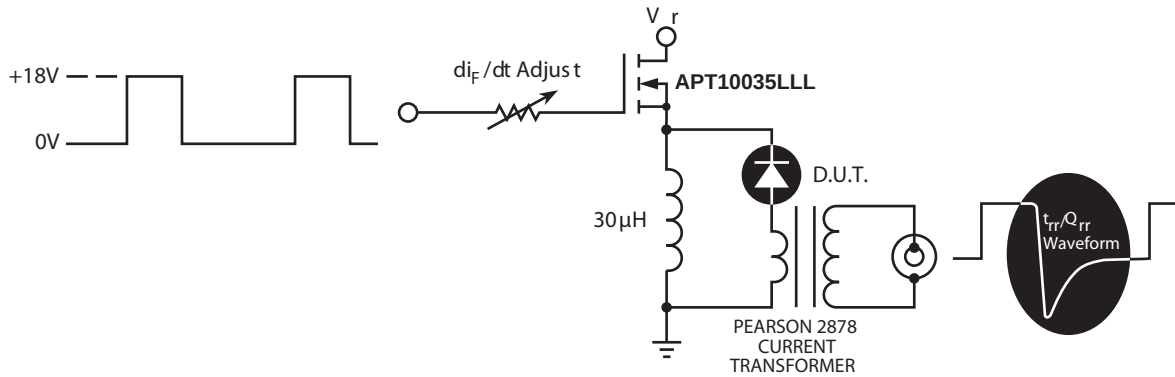


Fig. 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where the diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

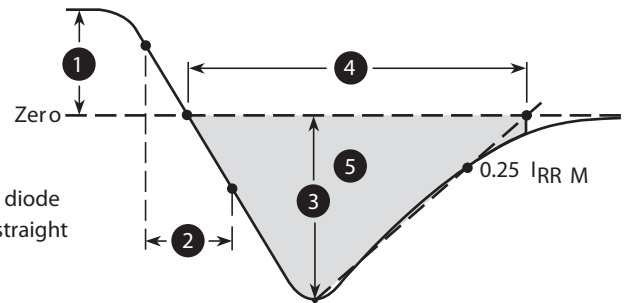
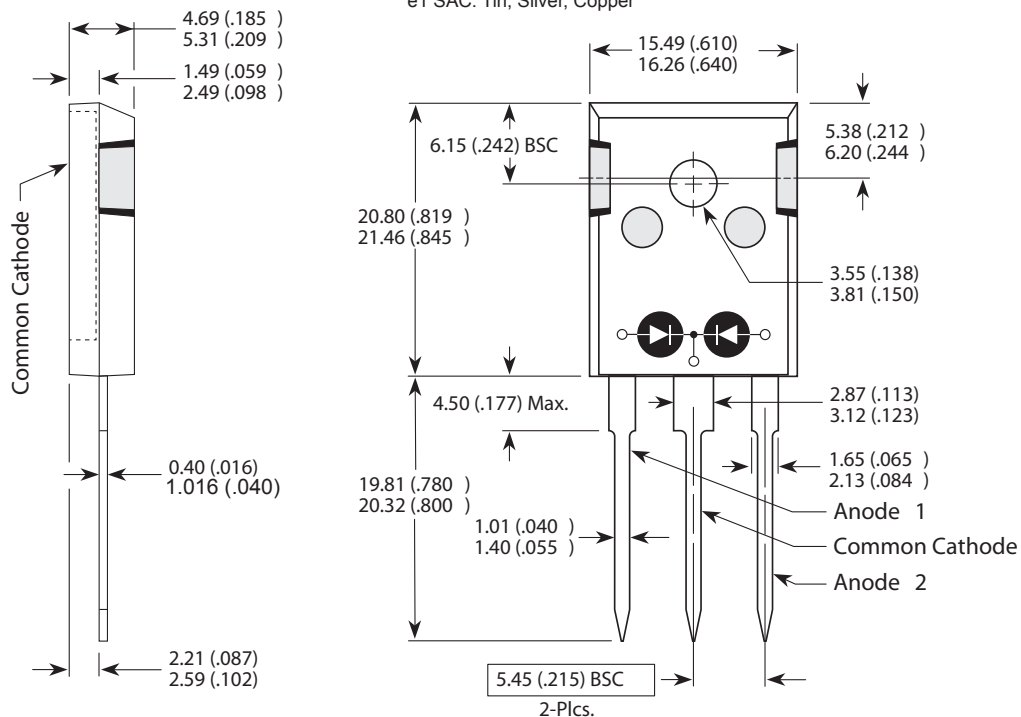


Fig. 10. Diode Reverse Recovery Waveform and Definition

TO-247 Package Outline

e1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)